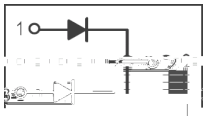
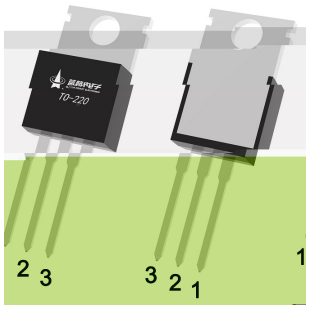
TO-220

Schottky Barrier Diode in a TO-220 Plastic Package.

Low power loss, high efficiency, HF Product.

For use in low voltage,high frequency inverters, free wheeling, and polarity protection applications.



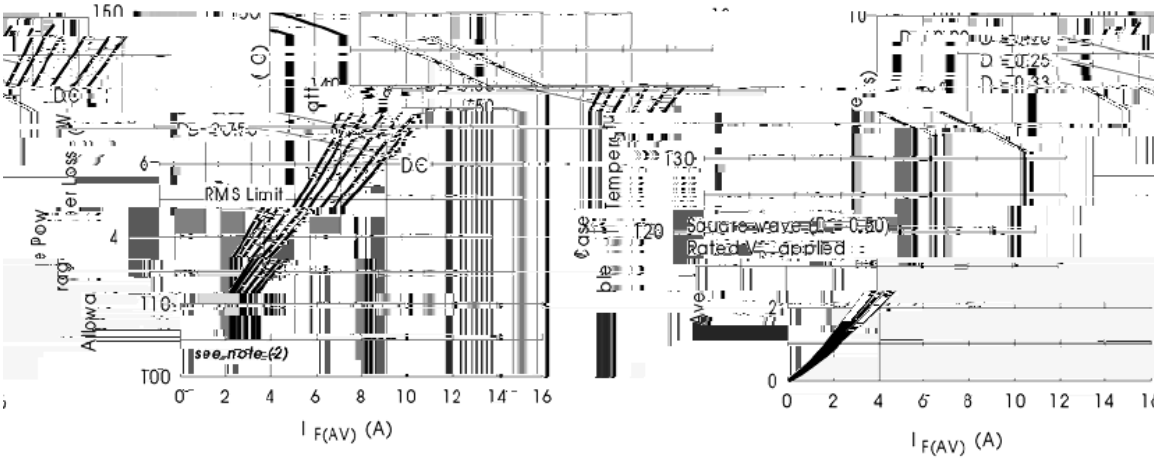


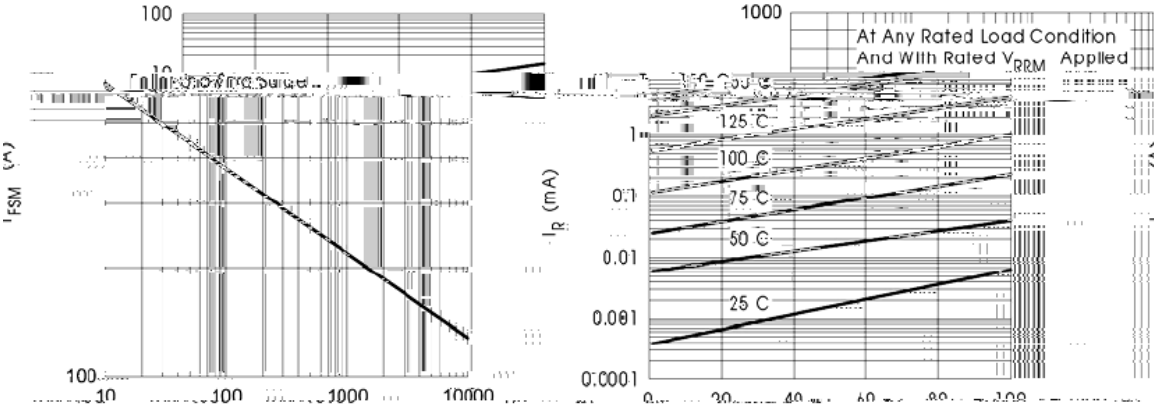
PIN1 Anode PIN 2 Cathode PIN 3 Anode

See Marking Instructions.

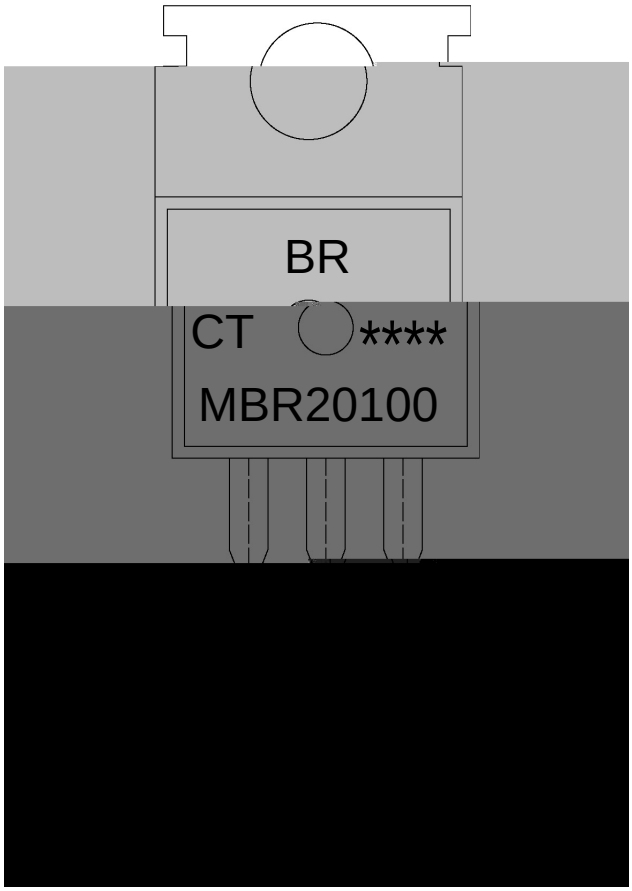
Parameter	Symbol	Rating	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	100	V
Peak Repetitive Forward Current	I_{FRM}	20	A
Average Rectified Forward Current	$I_{F(AV)}$	10	A
	$I_{F(AV)(total)}$	20	A
Non-Repetitive Peak Forward Surge Current	I_{FSM}	150	A
Repetitive Peak Reverse Surge Current	I_{RRM}	0.5	A
Thermal Resistance Junction to Case	$R_{\theta Jc}$	2.0	/W
Junction Temperature Range	T_j	175	
Storage Temperature Range	T_{stg}	-55 175	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Forward Voltage	V_F	I_F =10A(T_C=25)			0.85	V
		I_F =10A(T_C=125)			0.7	V
		I_F =20A(T_C=25)			0.95	V
		I_F =20A(T_C=125)			0.85	V
Instantaneous Reverse Current	I_R	V_R=100V(T_C=25)			0.15	mA
		V_R=100V(T_C=125)			150	mA
Voltage Rate of Change	dv/dt				10000	V/μs


RMS Limit
DC
see note (2)
I F(AV) (A)
Square wave (D = 0.80)
Rated V applied
I F(AV) (A)


At Any Rated Load Condition
And With Rated V RRM Applied
125 C
100 C
75 C
50 C
25 C


单位:
Max
Min
Max
9.0
9.4
15.7
1.22
1.32
0.4
0.6
2.34
2.74
4.3
4.7
1.25
1.45



BR

MBR20100

CT:

****

Note:

BR:	Company Code
MBR20100	Product Type Code
CT:	Internal Structure
****:	Lot No. Code, code change with Lot No.